

## 产品规格书

### Specifcation of products

产品名称:快恢复二极管

产品型号: MFK200U12-K2

浙江世菱半导体有限公司  
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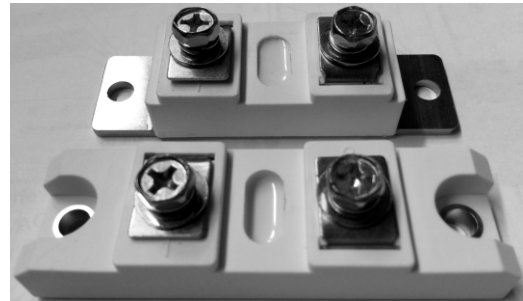
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林益龙	曹剑龙	宗瑞

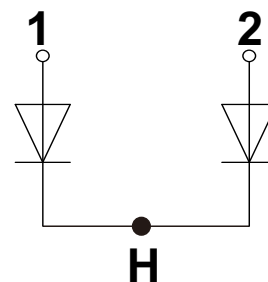
### PRODUCT FEATURES

- ☑ Ultrafast Reverse Recovery Time
- ☑ Soft Reverse Recovery Characteristics
- ☑ Low Reverse Recovery Loss
- ☑ Low Forward Voltage
- ☑ High Surge Current Capability
- ☑ Low Inductance Package



### APPLICATIONS

- ☑ Inversion Welder
- ☑ Uninterruptible Power Supply (UPS)
- ☑ Plating Power Supply
- ☑ Ultrasonic Cleaner and Welder
- ☑ Converter & Chopper
- ☑ Power Factor Correction (PFC) Circuit



### ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
$V_R$	Maximum D.C. Reverse Voltage		1200	V
$V_{RRM}$	Maximum Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	$T_C=110^{\circ}\text{C}$ , Per Diode	200	A
		$T_C=120^{\circ}\text{C}$ , 20KHz, Per Diode	150	A
$I_{F(RMS)}$	RMS Forward Current	$T_C=110^{\circ}\text{C}$ , Per Diode	280	A
$I_{FSM}$	Non-Repetitive Surge Forward Current	$T_J=45^{\circ}\text{C}$ , $t=10\text{ms}$ , 50Hz, Sine	1800	A
		$T_J=45^{\circ}\text{C}$ , $t=8.3\text{ms}$ , 60Hz, Sine	1950	A
$I^2t$	$I^2t$ (For Fusing)	$T_J=45^{\circ}\text{C}$ , $t=10\text{ms}$ , 50Hz, Sine	16200	$\text{A}^2\text{s}$
		$T_J=45^{\circ}\text{C}$ , $t=8.3\text{ms}$ , 60Hz, Sine	19012	$\text{A}^2\text{s}$
$P_D$	Power Dissipation		568	W
$T_J$	Junction Temperature		-40 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range		-40 to +125	$^{\circ}\text{C}$
$V_{isol}$	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
Torque	Module-to-Sink	Recommended (M6)	3~5	N.M
Torque	Module Electrodes	Recommended (M6)	3~5	N.M
$R_{\theta C}$	Thermal Resistance	Junction-to-Case	0.22	$^{\circ}\text{C} / \text{W}$
Weight			92	g

### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{RM}$	Reverse Leakage Current	$V_R=1200\text{V}$	--	--	2	mA
		$V_R=1200\text{V}, J=125^\circ\text{C}$	--	--	10	mA
$V_F$	Forward Voltage	$I_F=200\text{A}$	--	2.3	--	V
		$I_F=200\text{A}, T_J=125^\circ\text{C}$	--	1.9	--	V
$t_{rr}$	Reverse Recovery Time	$I_F=1\text{A}, V_R=30\text{V}, di_F/dt=-200\text{A}/\mu\text{s}$	--	57	--	ns
$t_{rr}$	Reverse Recovery Time	$V_R=600\text{V}, I_F=200\text{A}$	--	110	--	ns
$I_{RRM}$	Max. Reverse Recovery Current	$di_F/dt=-200\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$	--	9	--	A
$t_{rr}$	Reverse Recovery Time	$V_R=600\text{V}, I_F=200\text{A}$	--	500	--	ns
$I_{RRM}$	Max. Reverse Recovery Current	$di_F/dt=-200\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$	--	21	--	A

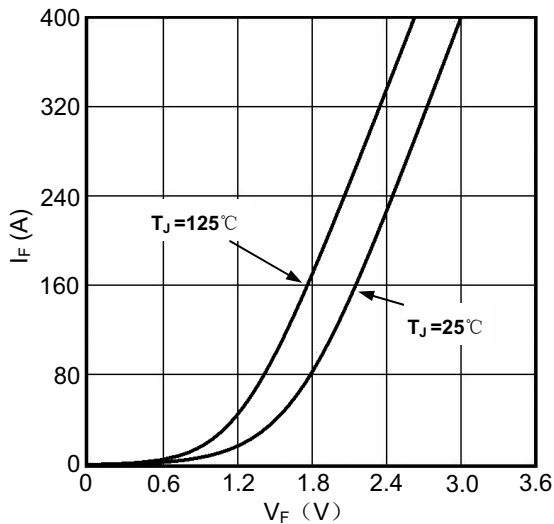


Figure1. Forward Voltage Drop vs Forward Current

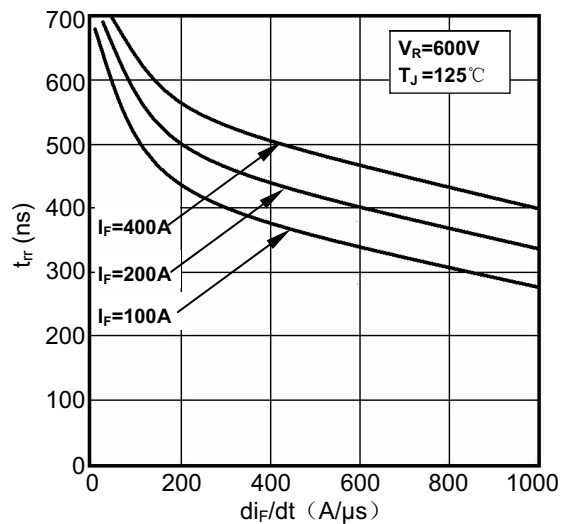


Figure2. Reverse Recovery Time vs  $di_F/dt$

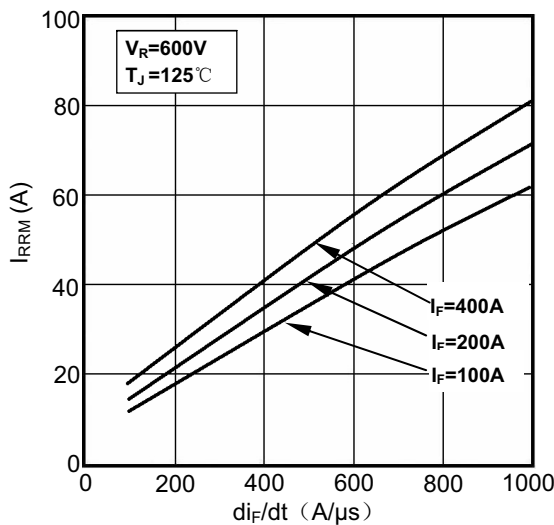


Figure3. Reverse Recovery Current vs  $di_F/dt$

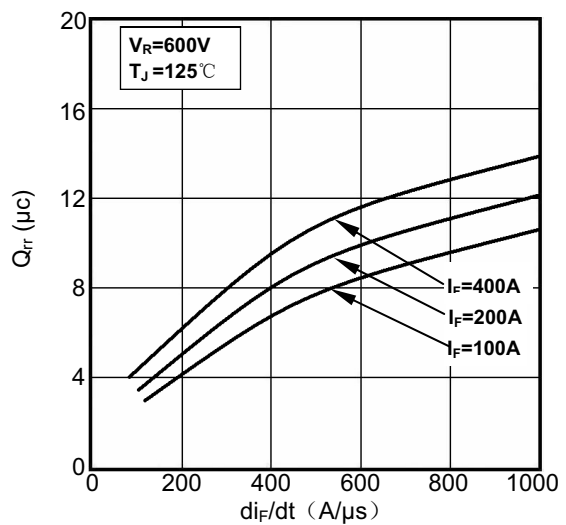


Figure4. Reverse Recovery Charge vs  $di_F/dt$

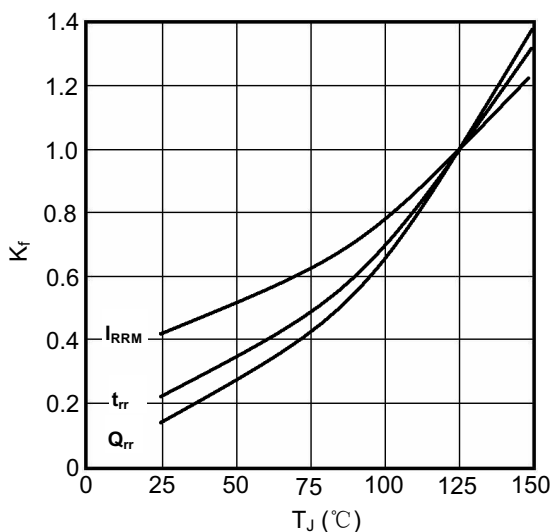


Figure5. Dynamic Parameters vs Junction Temperature

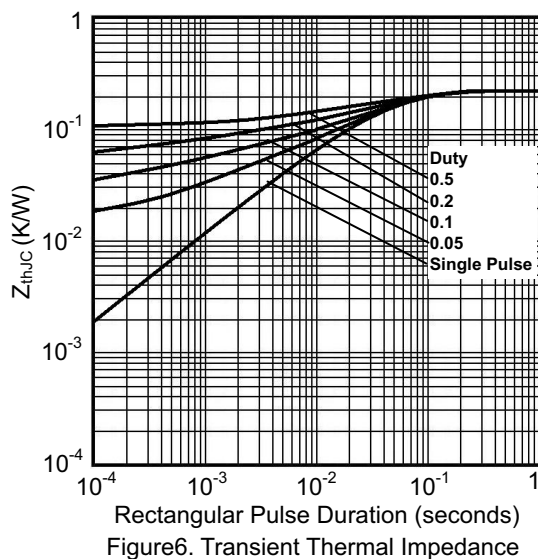
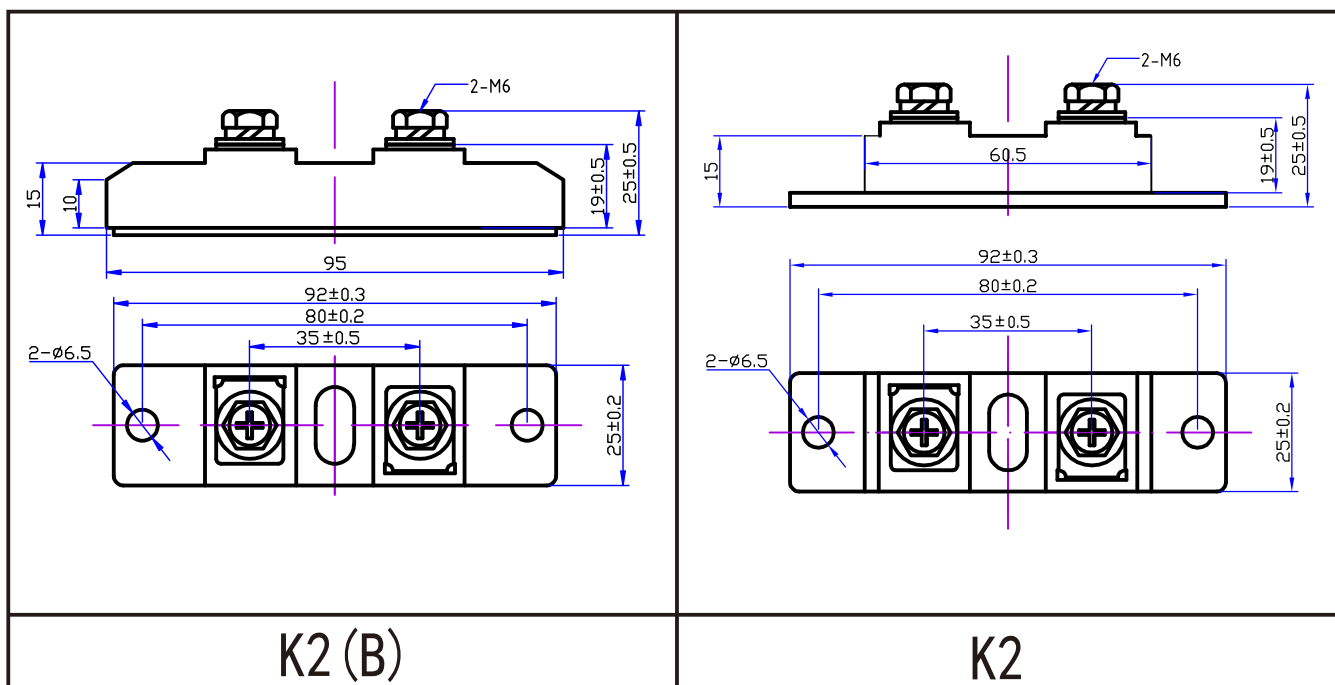


Figure6. Transient Thermal Impedance

### Package Outlines



Unit:mm